



# High Transfer Efficiency, General Purpose Type Photocoupler LTK4N32/LTK4N33

■ 8835547 0000010 2 ■

T-41-85

TAIWAN LITON ELECTRONIC

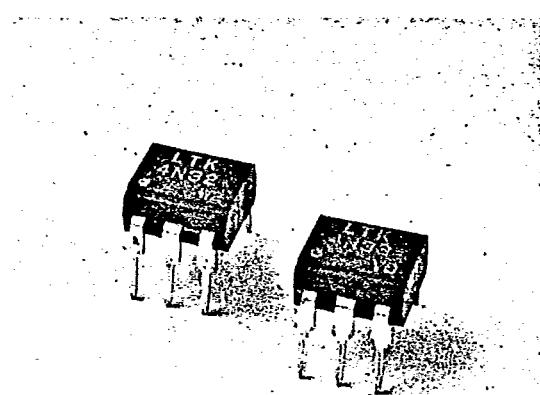
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## ■ FEATURES

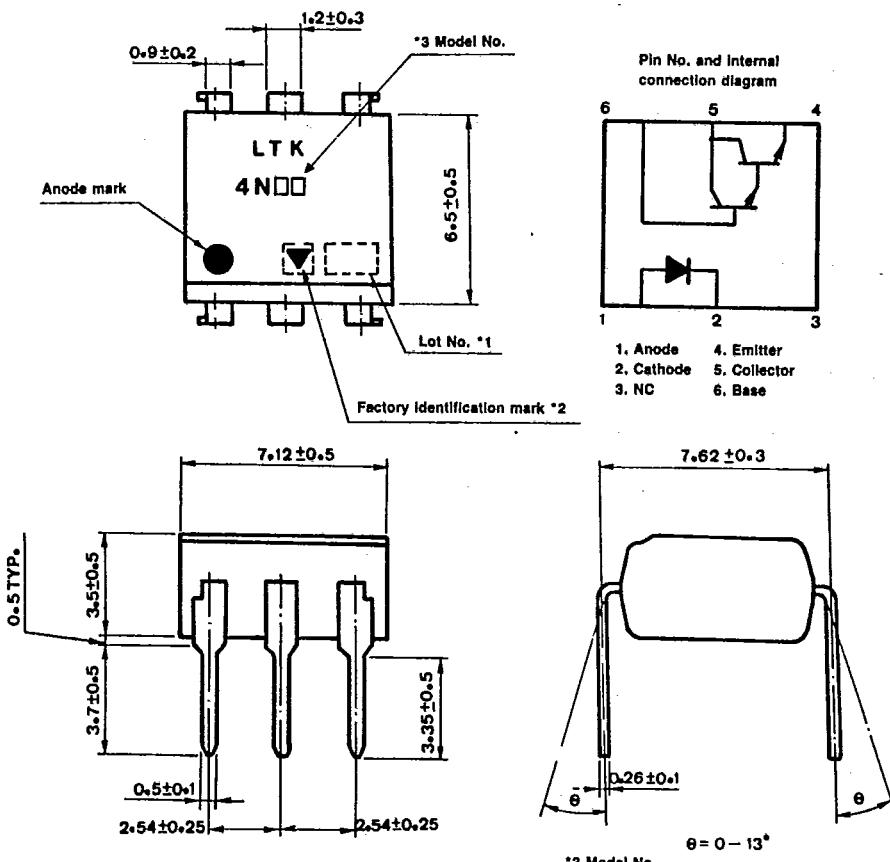
1. High current transfer ratio  
LTK4N32, LTK4N33  
(CTR:MIN. 500% at  $I_F = 10\text{mA}$ ,  $V_{CE} = 10\text{V}$ )
2. Response time  $t_{on}$ :MAX.  $5\mu\text{s}$  at  $I_F = 200\text{mA}$   
 $V_{CC} = 10\text{V}$ ,  $I_C = 50\text{mA}$
3. UL approved (No E113898 (S))

## ■ APPLICATIONS

1. I/O interfaces for computers
2. System appliances, measuring instruments
3. Signal transmission between circuits of different potentials and impedances



## ■ OUTLINE DIMENSIONS (UNIT: mm)



\*1 2-digit number marked according to DIN standard

\*2 Factory Identification mark shall be or shall not be marked.

**RATINGS AND CHARACTERISTICS****Absolute maximum ratings**

(Ta = 25°C)

Parameter		Symbol	Rating	Unit
Input	Forward current	I <sub>F</sub>	80	mA
	*1 Peak forward current	I <sub>FM</sub>	3	A
	Reverse voltage	V <sub>R</sub>	6	V
	Power dissipation	P	150	mW
Output	Collector-emitter voltage	V <sub>CCEO</sub>	30	V
	Collector-base voltage	V <sub>CBBO</sub>	30	V
	Emitter-collector voltage	V <sub>ECCO</sub>	5	V
	Collector current	I <sub>C</sub>	100	mA
	Collector power dissipation	P <sub>C</sub>	150	mW
Total power dissipation		P <sub>tot</sub>	250	mW
* 2 Isolation voltage	LTK4N32	V <sub>iso</sub>	2500	V <sub>rms</sub>
	LTK4N33		1500	
Operating temperature		T <sub>opr</sub>	-55 ~ +100	°C
Storage temperature		T <sub>stg</sub>	-55 ~ +150	°C
* 3 Soldering temperature		T <sub>sol</sub>	260	°C

\*1 Pulse width ≤ 1 μs Duty ratio:0.001

\*2 AC for 1 minute 40~60% RH

\*3 For 10 seconds

## • Electro-optical characteristics

(Ta = 25°C)

Parameter		Symbol	Min.	Typ.	Max.	Unit	Conditions
Input	Forward voltage	V <sub>F</sub>	—	1.2	1.5	V	I <sub>F</sub> = 10mA
	Reverse current	I <sub>R</sub>	—	—	10	μA	V <sub>R</sub> = 4V
	Terminal capacitance	C <sub>t</sub>	—	50	—	pF	V = 0, f = 1 kHz
Output	Collector dark current	I <sub>CEO</sub>	—	—	100	nA	V <sub>CE</sub> = 10V, I <sub>F</sub> = 0
	Collector-emitter breakdown voltage	BV <sub>CEO</sub>	30	—	—	V	I <sub>C</sub> = 0.1mA I <sub>F</sub> = 0
	Emitter-collector breakdown voltage	BV <sub>ECO</sub>	5	—	—	V	I <sub>E</sub> = 10μA I <sub>F</sub> = 0
	Collector-base breakdown voltage	BV <sub>CBO</sub>	30	—	—	V	I <sub>C</sub> = 0.1mA I <sub>F</sub> = 0
Transfer characteristics	*1 Collector current	I <sub>C</sub>	50	—	—	mA	I <sub>F</sub> = 10mA V <sub>CE</sub> = 10V
	Collector-emitter saturation voltage	V <sub>CE(sat)</sub>	—	—	1.0	V	I <sub>F</sub> = 8mA I <sub>C</sub> = 2mA
	Isolation resistance	R <sub>iso</sub>	5 × 10 <sup>10</sup>	1 × 10 <sup>11</sup>	—	Ω	DC500V 40 ~ 60% RH
	Floating capacitance	C <sub>f</sub>	—	1.0	—	pF	V = 0, f = 1MHz
	Response time (Turn-on time)	t <sub>on</sub>	—	—	5	μs	I <sub>F</sub> = 200mA (t <sub>w</sub> ≈ 1.0mS) V <sub>CC</sub> = 10V I <sub>C</sub> = 50mA
	Response time (Turn-off time)	t <sub>off</sub>	—	—	100	μs	

\*1 Pulse test: Input pulse width = 300μs Duty ratio ≤ 0.02, CTR =  $\frac{I_C}{I_F} \times 100\%$

**■ SUPPLEMENT****• Isolation voltage shall be measured in the following method.**

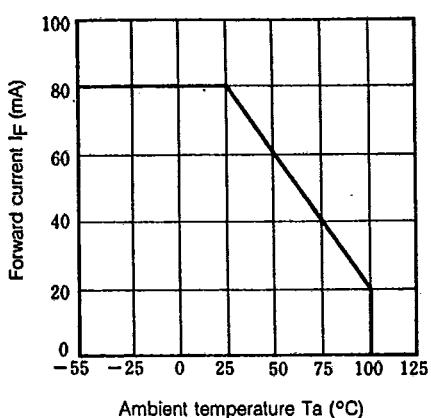
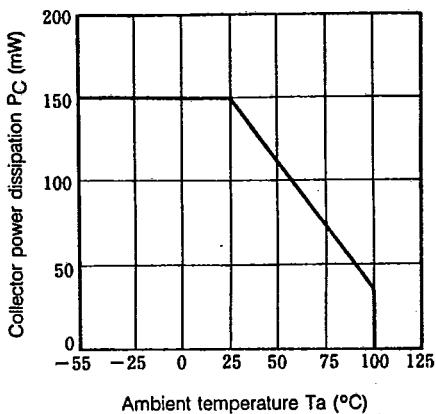
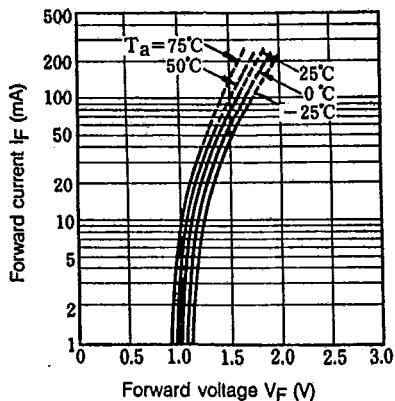
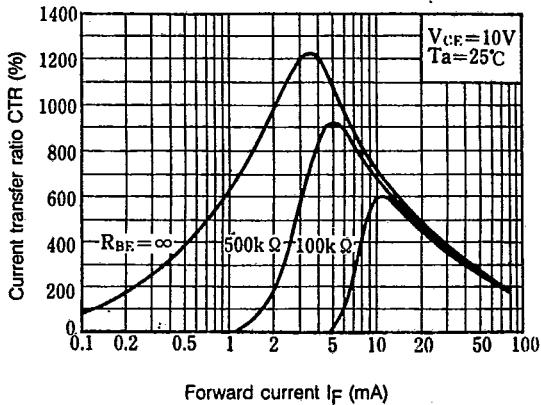
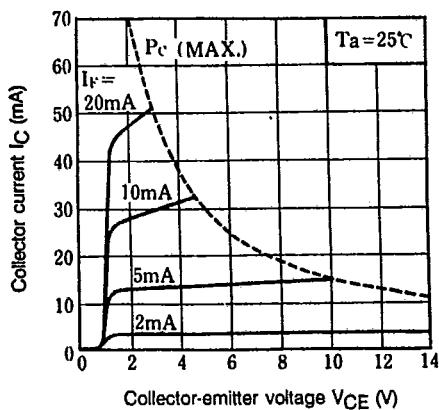
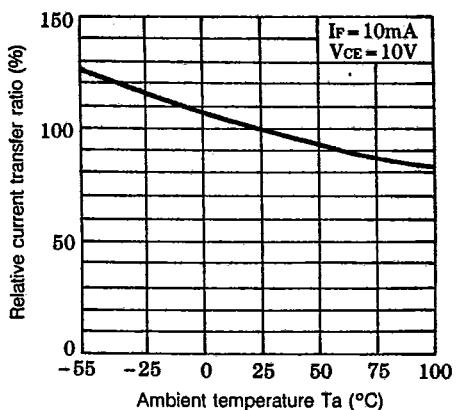
- (1) Short between anode and cathode on the primary side and between collector, emitter and base on the secondary side.
- (2) The isolation voltage tester with a zero-cross circuit shall be used.
- (3) The waveform of applied voltage shall be a sine wave.

**• Inspection standard**

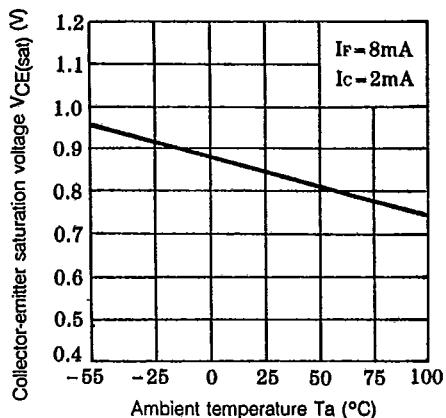
Outgoing inspection standard for LITON products are shown below.

- (1) A single sampling plan, normal inspection level II based on MIL-STD-105D is applied. The AQL according to the inspection items are shown below.

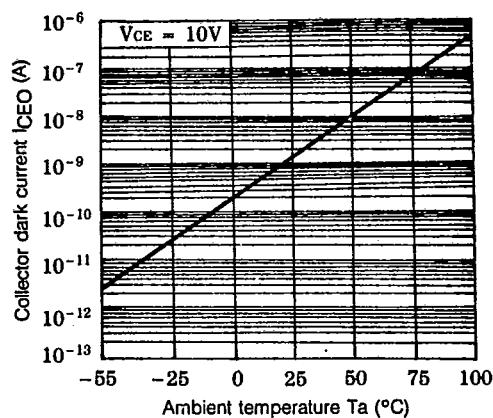
Defect	Inspection item	AQL(%)	Judgement criterion
Major defect	<ul style="list-style-type: none"><li>• Electrical characteristics</li><li>• Unreadable marking</li><li>• Open,short</li></ul>	0.25	Depend on the specification
Minor defect	<ul style="list-style-type: none"><li>• Appearance</li><li>• Dimension</li></ul>	0.4	

**Fig. 1** Forward Current vs. Ambient Temperature**Fig. 2** Collector Power Dissipation vs. Ambient Temperature**Fig. 3** Forward Current vs. Forward Voltage**Fig. 4** Current Transfer Ratio vs. Forward Current**Fig. 5** Collector Current vs. Collector-emitter Voltage**Fig. 6** Relative Current Transfer Ratio vs. Ambient Temperature

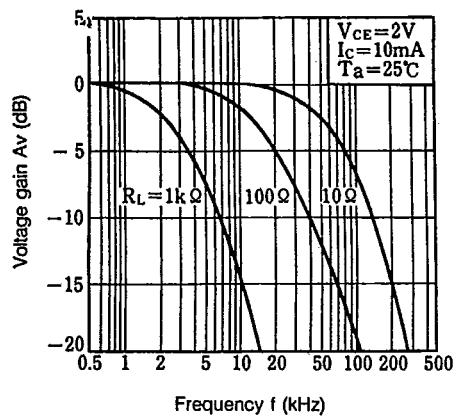
**Fig. 7** Collector-emitter Saturation Voltage vs.  
Ambient Temperature



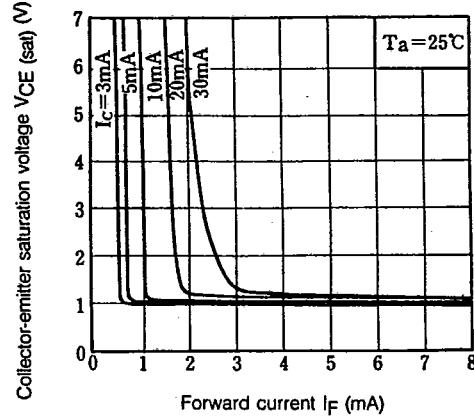
**Fig. 8** Collector Dark Current vs.  
Ambient Temperature



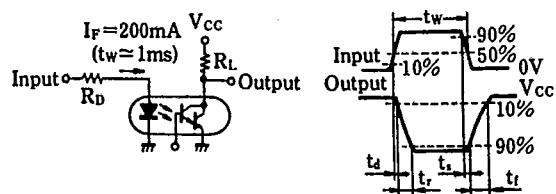
**Fig. 9** Frequency Response



**Fig. 10** Collector-emitter Saturation Voltage vs.  
Forward Current



**Fig.11** Test Circuit for Response Time



**Fig. 12** Test Circuit for Frequency Response

